Central™ Semiconductor Corp.

PROCESS CP591V

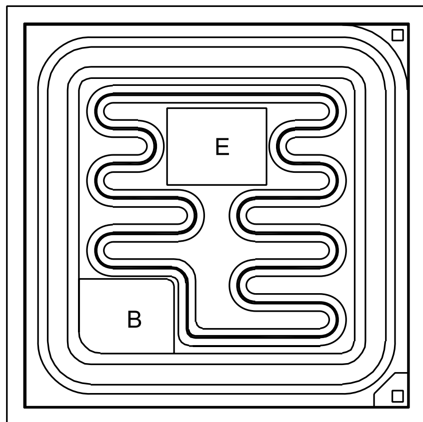
Small Signal Transistor

PNP - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19 x 19 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R1

GROSS DIE PER 4 INCH WAFER

30,475

PRINCIPAL DEVICE TYPES

2N2905A
2N2907A
CMPT2907A
CMST2907A
CXT2907A
CZT2907A
PN2907A

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Hauppauge, NY 11788 USA
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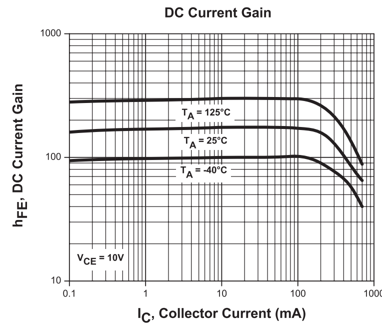
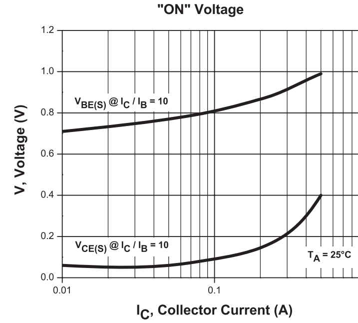
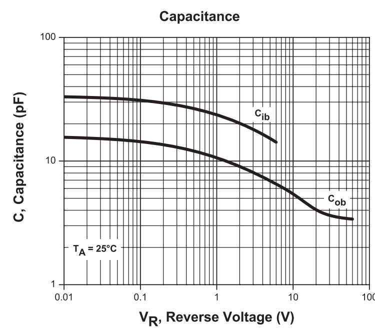
R2 (8-October 2008)

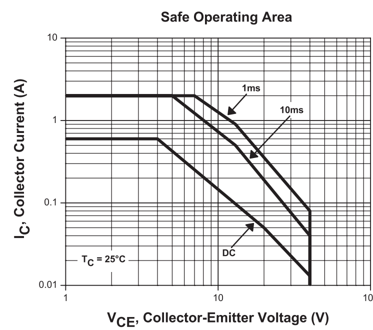
PROCESS CP591V

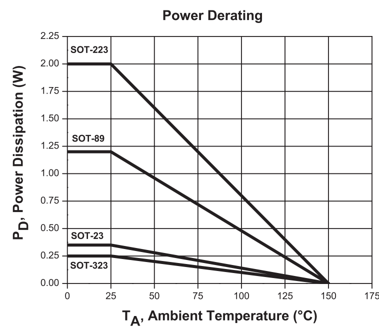
Typical Electrical Characteristics

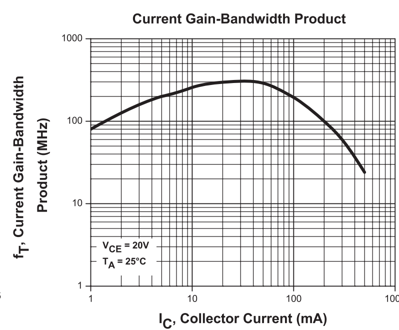












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